

Shigeki Sakai

List of Publications by Year in descending order

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144
papers

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citations

236925

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146
all docs

146
docs citations

146
times ranked

1489
citing authors

#	ARTICLE	IF	CITATIONS
1	Fluxons in thin-film superconductor-insulator superlattices. Journal of Applied Physics, 1993, 73, 2411-2418.	2.5	391
2	Dynamic behavior of Josephson-coupled layered structures. Physical Review B, 1994, 50, 3942-3952.	3.2	205
3	Metal-Ferroelectric-Insulator-Semiconductor Memory FET With Long Retention and High Endurance. IEEE Electron Device Letters, 2004, 25, 369-371.	3.9	200
4	Leakage current of multiferroic (Bi _{0.6} Tb _{0.3} La _{0.1})FeO ₃ thin films grown at various oxygen pressures by pulsed laser deposition and annealing effect. Journal of Applied Physics, 2006, 99, 054104.	2.5	165
5	Theory and experiment on electromagnetic-wave-propagation velocities in stacked superconducting tunnel structures. Physical Review B, 1994, 50, 12905-12914.	3.2	154
6	Self-Aligned-Gate Metal/Ferroelectric/Insulator/Semiconductor Field-Effect Transistors with Long Memory Retention. Japanese Journal of Applied Physics, 2005, 44, L800-L802.	1.5	114
7	Recent Progress of Ferroelectric-Gate Field-Effect Transistors and Applications to Nonvolatile Logic and FeNAND Flash Memory. Materials, 2010, 3, 4950-4964.	2.9	66
8	Ferroelectric-Gate Field Effect Transistor Memories. Topics in Applied Physics, 2016, , .	0.8	62
9	Memory properties of SrBi ₂ Ta ₂ O ₉ thin films prepared on SiO ₂ /Si substrates. Applied Physics Letters, 1999, 75, 1613-1615.	3.3	61
10	Submillimeter-band high-power generation using multilayered Josephson junctions. Applied Physics Letters, 1998, 73, 686-688.	3.3	57
11	Pt/SrBi ₂ Ta ₂ O ₉ /Hf-Al-O/Si Field-Effect-Transistor with Long Retention Using Unsaturated Ferroelectric Polarization Switching. Japanese Journal of Applied Physics, 2004, 43, 7876-7878.	1.5	54
12	Characterization of Pt-SrBi ₂ Ta ₂ O ₉ -Hf-Al-O-Si field-effect transistors at elevated temperatures. Applied Physics Letters, 2006, 89, 222910.	3.3	50
13	Josephson plasma resonance in superconducting multilayers. Physical Review B, 1998, 58, 2820-2826.	3.2	43
14	Bunched fluxon states in one-dimensional Josephson-junction arrays. Physical Review B, 1998, 57, 11691-11697.	3.2	38
15	Numerical study of fluxon dynamics in a system of two-stacked Josephson junctions. Journal of Applied Physics, 1995, 77, 1171-1177.	2.5	37
16	Self-limiting process for the bismuth content in molecular beam epitaxial growth of Bi ₂ Sr ₂ CuO _y thin films. Applied Physics Letters, 1997, 71, 3712-3714.	3.3	36
17	64 kbit Ferroelectric-Gate-Transistor-Integrated NAND Flash Memory with 7.5 V Program and Long Data Retention. Japanese Journal of Applied Physics, 2012, 51, 04DD01.	1.5	34
18	Unified theory for magnetic and electric field coupling in multistacked Josephson junctions. Physical Review B, 2004, 70, .	3.2	33

#	ARTICLE	IF	CITATIONS
19	Operational method of a ferroelectric (Fe)-NAND flash memory array. <i>Semiconductor Science and Technology</i> , 2009, 24, 105029.	2.0	32
20	Real time fluxon dynamics in Josephson transmission line. <i>IEEE Transactions on Magnetics</i> , 1985, 21, 737-740.	2.1	31
21	Super-relativistic fluxon in a Josephson multilayer: Experiment and simulation. <i>Physical Review B</i> , 2002, 66, .	3.2	30
22	Highly Scalable Fe(Ferroelectric)-NAND Cell with MFIS(Metal-Ferroelectric-Insulator-Semiconductor) Structure for Sub-10nm Tera-Bit Capacity NAND Flash Memories. , 2008, , .		30
23	Large-area pulsed-laser deposition of dielectric and ferroelectric thin films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2007, 25, 903-907.	2.1	29
24	Lowered operation voltage in Pt/SBi ₂ Ta ₂ O ₉ /HfO ₂ /Si ferroelectric-gate field-effect transistors by oxynitriding Si. <i>Semiconductor Science and Technology</i> , 2010, 25, 055005.	2.0	29
25	Basic operation of novel ferroelectric CMOS circuits. <i>Electronics Letters</i> , 2008, 44, 467.	1.0	27
26	Perturbation analysis of a parametrically changed sine-Gordon equation. <i>Physical Review B</i> , 1987, 36, 217-225.	3.2	25
27	Threshold voltage adjustment of ferroelectric-gate field effect transistors by ion implantation. <i>Semiconductor Science and Technology</i> , 2009, 24, 025012.	2.0	25
28	Epitaxial Bi ₄ Ti ₃ O ₁₂ thin film growth using Bi self-limiting function. <i>Journal of Crystal Growth</i> , 1999, 200, 161-168.	1.5	24
29	A Direct Coupled Josephson Sampler. <i>Japanese Journal of Applied Physics</i> , 1983, 22, L435-L437.	1.5	23
30	Molecular Beam Epitaxy Fabrication of SrTiO ₃ and Bi ₂ Sr ₂ CaCu ₂ O ₈ Heterostructures Using a Novel Reflection High-Energy Electron Diffraction Monitoring Technique. <i>Japanese Journal of Applied Physics</i> , 1992, 31, L949-L952.	1.5	23
31	Dynamics of multiple-junction stacked flux-flow oscillators: Comparison between theory and experiment. <i>Physical Review B</i> , 1998, 58, 5777-5782.	3.2	23
32	Atomic absorption spectroscopy system for flux monitoring and atomic-layer control of molecular beam epitaxial growth of BiSrCaCuO. <i>Review of Scientific Instruments</i> , 1997, 68, 2850-2855.	1.3	22
33	Epitaxial structure SrTiO ₃ on Si. <i>Journal of Applied Physics</i> , 2001, 89, 5421-5424.	2.5	21
34	Fluxon Observation Using a Josephson Sampler. <i>Japanese Journal of Applied Physics</i> , 1983, 22, L479-L481.	1.5	20
35	Theoretical study of electric-field effects in high-T _c oxide superconductors using an ultrathin-metal-insulator superlattice model. <i>Physical Review B</i> , 1993, 47, 9042-9047.	3.2	20
36	Temperature dependence of composition ratio of Bi ₂ Sr ₂ CaCu ₂ O ₈ + δ film by PLD method. <i>Physica C: Superconductivity and Its Applications</i> , 2004, 412-414, 1354-1357.	1.2	20

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37	Threshold-voltage distribution of Pt/SrBi ₂ Ta ₂ O ₉ /HfO ₂ /Si MFIS FETs. Semiconductor Science and Technology, 2008, 23, 045011.	2.0	20
38	Fabrication and characterization of sub-0.6- μ m ferroelectric-gate field-effect transistors. Semiconductor Science and Technology, 2010, 25, 115013.	2.0	20
39	Fluxon Feedback Oscillator. Japanese Journal of Applied Physics, 1984, 23, L610-L612.	1.5	19
40	Memory window widening of Pt/SrBi ₂ Ta ₂ O ₉ /HfO ₂ /Si ferroelectric-gate field-effect transistors by nitriding Si. Semiconductor Science and Technology, 2009, 24, 105026.	2.0	19
41	Ferroelectric (Fe)-NAND Flash Memory With Batch Write Algorithm and Smart Data Store to the Nonvolatile Page Buffer for Data Center Application High-Speed and Highly Reliable Enterprise Solid-State Drives. IEEE Journal of Solid-State Circuits, 2010, 45, 2156-2164.	5.4	18
42	Analytical Solutions of Traveling Fluxon Waves on a Josephson Transmission Line with Shunt Conductance and Uniform Bias Current. Japanese Journal of Applied Physics, 1983, 22, 1374-1381.	1.5	17
43	Analytic solution for fluxons in a long Josephson junction with surface losses. Physical Review B, 1986, 34, 3506-3509.	3.2	17
44	Direct observation of fluxon reflection in a Josephson transmission line. Physical Review B, 1987, 35, 5357-5360.	3.2	17
45	FeCMOS logic inverter circuits with nonvolatile-memory function. IEICE Electronics Express, 2009, 6, 831-836.	0.8	17
46	Electrical properties of ferroelectric-gate FETs with SrBi ₂ Ta ₂ O ₉ formed using MOCVD technique. Applied Physics A: Materials Science and Processing, 2012, 108, 835-842.	2.3	17
47	100-nm-size ferroelectric-gate field-effect transistor with 10 ⁸ -cycle endurance. Japanese Journal of Applied Physics, 2015, 54, 088004.	1.5	16
48	Energy band of ternary alloy semiconductors—Calculation by a coherent-potential approximation based on the method of linear combination of bond orbitals. Journal of Applied Physics, 1979, 50, 4143-4155.	2.5	15
49	FeFET Logic Circuits for Operating A 64 kb FeNAND Flash Memory Array. Integrated Ferroelectrics, 2012, 132, 114-121.	0.7	15
50	Plasma resonance in anisotropic layered high-T _c superconductors. Physical Review B, 1999, 60, 9810-9816.	3.2	14
51	Particle-free superconducting Bi ₂ Sr ₂ CaCu ₂ O _x ultrathin films prepared by atomic-layer-controlled molecular beam epitaxy technique. Physica C: Superconductivity and Its Applications, 1999, 311, 42-48.	1.2	14
52	Memory properties of a ferroelectric gate field-effect transistor with an adjoining metal-ferroelectric-metal assistance cell. Journal of Applied Physics, 2003, 94, 2559-2562.	2.5	14
53	Electrical properties of Ca _x Sr _{1-x} Bi ₂ Ta ₂ O ₉ ferroelectric-gate field-effect transistors. Semiconductor Science and Technology, 2013, 28, 085003.		14
54	Fluxon Transfer Device. Japanese Journal of Applied Physics, 1985, 24, L771-L773.	1.5	13

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55	Molecular beam epitaxial growth of SrO and CaO with RHEED intensity oscillation. Journal of Low Temperature Physics, 1996, 105, 1337-1342.	1.4	13
56	All-perovskite-oxide ferroelectric memory transistor composed of Bi ₂ Sr ₂ CuO _x and PbZr _{0.5} Ti _{0.5} O ₃ films. Journal of Applied Physics, 2001, 89, 8153-8158.	2.5	13
57	Millimeter-wave radiation from a Teflon dielectric probe and its imaging application. Measurement Science and Technology, 2008, 19, 115501.	2.6	13
58	Downsizing of Ferroelectric-Gate Field-Effect-Transistors for Ferroelectric-NAND Flash Memory Cells. , 2011, , .		13
59	In-situ growth of Bi-Sr-Ca-Cu oxide superconducting thin films by molecular beam epitaxy with a pure ozone source. Journal of Crystal Growth, 1991, 115, 758-761.	1.5	12
60	Pulsed laser deposition and ferroelectric properties of SrBi ₂ Ta ₂ O ₉ thin films. Materials Letters, 1999, 38, 406-412.	2.6	12
61	Face-to-face annealing of Bi ₂ Sr ₂ CaCu ₂ O _x thin films for intrinsic Josephson junctions with uniform critical currents. Physica C: Superconductivity and Its Applications, 2005, 426-431, 1474-1478.	1.2	12
62	64 kbit Ferroelectric-Gate-Transistor-Integrated NAND Flash Memory with 7.5 V Program and Long Data Retention. Japanese Journal of Applied Physics, 2012, 51, 04DD01.	1.5	12
63	RHEED Intensity Monitored Growth of Bi-Sr-Ca-Cu-O Superconductors. Japanese Journal of Applied Physics, 1992, 31, L399-L401.	1.5	11
64	3.3 V write-voltage Ir/Ca _{0.2} /Sr _{0.8} /Bi ₂ /Ta ₂ /O ₉ /HfO ₂ /Si ferroelectric-gate field-effect transistors with 10 ⁹ endurance and good retention. Japanese Journal of Applied Physics, 2017, 56, 04CE04.	1.5	11
65	Area-Scalable 109-Cycle-High-Endurance FeFET of Strontium Bismuth Tantalate Using a Dummy-Gate Process. Nanomaterials, 2021, 11, 101.	4.1	11
66	Optical Properties of Vacuum-Deposited CdCr ₂ Se ₄ Thin Film. Japanese Journal of Applied Physics, 1976, 15, 2023-2024.	1.5	10
67	Growth Style of Bi ₄ Ti ₃ O ₁₂ Thin Films on CeO ₂ /Ce _{0.12} Zr _{0.88} O ₂ Buffered Si Substrates. Japanese Journal of Applied Physics, 1999, 38, 5411-5416.	1.5	10
68	Fabrication and critical currents of thin-film-type Bi ₂ Sr ₂ CaCu ₂ O _x intrinsic Josephson junctions. Physica C: Superconductivity and Its Applications, 2001, 362, 256-260.	1.2	10
69	Optimum ambient N ₂ pressure during HfAlO pulsed-laser deposition in Pt•SBT•HfAlO•Si field effect transistors. Journal of Vacuum Science & Technology B, 2008, 26, 1585.	1.3	10
70	Fabrication of thin-film-type Bi ₂ Sr ₂ CaCu ₂ O ₈ +Î intrinsic Josephson junctions by pulsed-laser-deposition. Superconductor Science and Technology, 2009, 22, 125004.	3.5	10
71	A 1.0V power supply, 9.5GByte/sec write speed, Single-Cell Self-Boost program scheme for Ferroelectric NAND Flash SSD. , 2010, , .		10
72	Maximum supercurrent in two Josephson-junction stacks: Theory and experiment. Physical Review B, 1998, 58, 6497-6505.	3.2	9

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73	Flux-flow cavity resonance modes in intrinsic Josephson junctions by Bi ₂ Sr ₂ CaCu ₂ O _x thin films. Physica C: Superconductivity and Its Applications, 2002, 367, 404-409.	1.2	9
74	Growth and characterization of potassium tantalate niobate single crystals by the step-cooling technique. Journal of Crystal Growth, 2002, 237-239, 694-699.	1.5	9
75	Properties of a dielectric probe for scanning near-field millimeter-wave microscopy. Journal of Applied Physics, 2006, 99, 056105.	2.5	9
76	Travelling Waves on a Josephson Transmission Line. Japanese Journal of Applied Physics, 1983, 22, 161-170.	1.5	8
77	Long-retention ferroelectric-gate FET with a (HfO ₂) _x (Al ₂ O ₃) _{1-x} buffer-insulating layer for 1T FeRAM. , 0, , .		8
78	A 0.5V operation, 32% lower active power, 42% lower leakage current, ferroelectric 6T-SRAM with V _{th} self-adjusting function for 60% larger Static Noise Margin. , 2009, , .		8
79	Novel process for widening memory window of sub-200 nm ferroelectric-gate field-effect transistor by ferroelectric coating the gate-stack sidewall. Semiconductor Science and Technology, 2015, 30, 015024.	2.0	8
80	Criteria for fluxon generation in long Josephson junctions by current pulses. Applied Physics Letters, 1987, 50, 1107-1109.	3.3	7
81	Bunching of Solitons in Long Josephson Junctions. Japanese Journal of Applied Physics, 1987, 26, 1579.	1.5	7
82	A zero V _{th} ; memory cell ferroelectric-NAND flash memory with 32% read disturb, 24% program disturb, 10% data retention improvement for enterprise SSD. , 2009, , .		7
83	Large grain growth by annealing of Ag-covered Bi ₂ Sr ₂ CaCu ₂ O ₈ + δ thin films and its application in the fabrication of intrinsic Josephson junctions. Superconductor Science and Technology, 2010, 23, 115006.	3.5	7
84	A 1.0V power supply, 9.3GB/s write speed, Single-Cell Self-Boost program scheme for high performance ferroelectric NAND flash SSD. Solid-State Electronics, 2011, 58, 34-41.	1.4	7
85	Downsizing and memory array integration of Pt/SrBi ₂ Ta ₂ O ₉ /Hf-Al-O/Si ferroelectric-gate field-effect transistors. , 2012, , .		7
86	Method for disclosing invisible physical properties in metal-ferroelectric-insulator-semiconductor gate stacks. Journal Physics D: Applied Physics, 2017, 50, 165107.	2.8	7
87	High-Endurance Ferroelectric NOR Flash Memory Using (Ca,Sr)Bi ₂ Ta ₂ O ₉ FeFETs. , 2018, , .		7
88	Investigation of Ferroelectric Grain Sizes and Orientations in Pt/CaxSr _{1-x} Bi ₂ Ta ₂ O ₉ /Hf-Al-O/Si High Performance Ferroelectric-Gate Field-Effect-Transistors. Materials, 2019, 12, 399.	2.9	7
89	Compact model of ferroelectric-gate field-effect transistor for circuit simulation based on multidomain Landau-Khalatnikov theory. Japanese Journal of Applied Physics, 2017, 56, 04CE07.	1.5	7
90	Nb/GaAs super-Schottky diode. IEEE Electron Device Letters, 1980, 1, 236-238.	3.9	6

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91	Analytic solutions for bunched two-fluxon states in Josephson transmission lines. <i>Physical Review B</i> , 1987, 36, 812-814.	3.2	6
92	Epitaxial Growth of Bi ₄ Ti ₃ O ₁₂ /CeO ₂ /Ce _{0.12} Zr _{0.88} O ₂ and Bi ₄ Ti ₃ O ₁₂ /SrTiO ₃ /Ce _{0.12} Zr _{0.88} O ₂ Thin Films on Si and Its Application to Metal-Ferroelectric-Insulator-Semiconductor Diodes. <i>Japanese Journal of Applied Physics</i> , 2000, 39, 5505-5511.	1.5	6
93	Effect of Nitrogen Inclusion into Hf-Al-O Layer on Device Properties of Pt/SrBi ₂ Ta ₂ O ₉ /Hf-Al-O/Si Diodes. <i>Funtai Oyobi Fumatsu Yakin/Journal of the Japan Society of Powder and Powder Metallurgy</i> , 2008, 55, 17-20.	0.2	6
94	0.5V Bit-Line-Voltage Self-Boost-Programming in Ferroelectric-NAND Flash Memory. , 2011, , .		6
95	Static characteristic of a new quasiparticle injected superconducting weak link device. <i>Electronics Letters</i> , 1981, 17, 501.	1.0	5
96	Fluxon Waves on a Josephson Transmission Line. <i>Japanese Journal of Applied Physics</i> , 1982, 21, L7-L9.	1.5	5
97	Epitaxial structure SrBi ₂ Ta ₂ O ₉ <116> /SrTiO ₃ <011> /Ce _{0.12} Zr _{0.88} O ₂ <001> /Si<001> for ferroelectric-gate FET memory. <i>Integrated Ferroelectrics</i> , 2001, 40, 135-143.	0.7	5
98	Characteristics of intrinsic Josephson junctions using a Bi ₂ Sr ₂ CaCu ₂ O _x thin film estimated overall in a chip. <i>Physica C: Superconductivity and Its Applications</i> , 2004, 412-414, 1410-1413.	1.2	5
99	A 1.2 V Power Supply, 2.43 Times Power Efficient, Adaptive Charge Pump Circuit with Optimized Threshold Voltage at Each Pump Stage for Ferroelectric-NAND Flash Memories. <i>Japanese Journal of Applied Physics</i> , 2010, 49, 04DD10.	1.5	5
100	A Negative Word-Line Voltage Negatively-Incremental Erase Pulse Scheme with $\hat{I}^n V_{TH} = 1/6 \hat{I}^n V_{ERASE}$ for Enterprise Solid-State Drive Application Ferroelectric-NAND Flash Memories. <i>Japanese Journal of Applied Physics</i> , 2010, 49, 04DD08.	1.5	5
101	Analytical and numerical results for a long Josephson junction with surface losses. <i>IEEE Transactions on Magnetics</i> , 1987, 23, 1114-1117.	2.1	4
102	Atomic layer by atomic layer growth of Bi—, Sr—, Ca—, Cu oxide superconducting thin films by molecular beam epitaxy. <i>Physica C: Superconductivity and Its Applications</i> , 1991, 185-189, 2013-2014.	1.2	4
103	Nanometer level etching and deposition of Bi-Sr-Ca-Cu-O superconducting thin films. , 1996, , .		4
104	A Digital Method of Gas Laser Etching for Oxide Superconductors. <i>Japanese Journal of Applied Physics</i> , 1996, 35, L94-L96.	1.5	4
105	Prediction of half harmonic generation in stacked Josephson junctions and Bi ₂ Sr ₂ CaCu ₂ O _x single crystals. <i>Physical Review B</i> , 2000, 61, 11328-11331.	3.2	4
106	Growth of Single Phase Bi ₂ Sr ₂ CaCu ₂ O _x Whiskers Using Optimized Starting Compositions for Glassy Precursors. <i>Japanese Journal of Applied Physics</i> , 2003, 42, 5022-5023.	1.5	4
107	Growth of High-Quality Single-Phase Bi ₂ Sr ₂ CaCu ₂ O _x Whiskers by a New Growth "Melt" Regrowth Method. <i>Japanese Journal of Applied Physics</i> , 2004, 43, 3378-3380.	1.5	4
108	Resonant characteristics of twofold Josephson junctions with various critical current ratio. <i>Physica C: Superconductivity and Its Applications</i> , 2004, 412-414, 1468-1472.	1.2	4

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109	A 0.5-V Six-Transistor Static Random Access Memory with Ferroelectric-Gate Field Effect Transistors. Japanese Journal of Applied Physics, 2010, 49, 121501.	1.5	4
110	Recent Advances in Ferroelectric-Gate Field-Effect-Transistor Technology. Integrated Ferroelectrics, 2011, 124, 140-146.	0.7	4
111	Fluxon Divider. Japanese Journal of Applied Physics, 1985, 24, L749-L751.	1.5	3
112	Rheed Intensity Monitored Growth of Bi-Sr-Ca-Cu-O Superconductors. Materials Research Society Symposia Proceedings, 1992, 275, 73.	0.1	3
113	Plasma resonance and flux dynamics in layered high-T _c superconductors. Physica C: Superconductivity and Its Applications, 2000, 332, 297-301.	1.2	3
114	Description of intrinsic Josephson junctions by the inductive coupling theory. Physica C: Superconductivity and Its Applications, 2001, 362, 1-9.	1.2	3
115	Theoretical and numerical study on multistacked Josephson junctions with a parametric modulation of their critical currents. Physical Review B, 2005, 72, .	3.2	3
116	Gate Materials and Fabrication-Processes of Metal-Ferroelectric-Insulator-Semiconductor Memory FETs with Long Data Retention. Advances in Science and Technology, 2006, 45, 2382.	0.2	3
117	Improvement of Read Disturb, Program Disturb and Data Retention by Memory Cell VTH Optimization of Ferroelectric (Fe)-NAND Flash Memories for Highly Reliable and Low Power Enterprise Solid-State Drives (SSDs). IEICE Transactions on Electronics, 2011, E94-C, 539-547.	0.6	3
118	Dynamic Analog Characteristics of 10 ⁹ Cycle-Endurance Low-Voltage Nonvolatile Ferroelectric-Gate Memory Transistors. , 2017, , .		3
119	A time-domain analog weighted-sum calculation circuit using ferroelectric-gate field-effect transistors for artificial intelligence processors. Japanese Journal of Applied Physics, 2020, 59, 040604.	1.5	3
120	Quasiparticle-Injected Superconducting Weak Link Device. Japanese Journal of Applied Physics, 1982, 21, 331.	1.5	3
121	Laser Etching of Bi-Sr-Ca-Cu-O Superconducting Thin Films. Japanese Journal of Applied Physics, 1991, 30, L355-L357.	1.5	2
122	Quasiparticle-Injected Superconducting Weak Link Device. , 1981, , .		2
123	Digital laser etching of Bi-Sr-Ca-Cu-O superconducting thin films. Thin Solid Films, 1996, 281-282, 513-516.	1.8	1
124	Fabrication and Electrical Characteristics of a Trench-Type Metal-Ferroelectric-Metal-Insulator-Semiconductor Field Effect Transistor. Japanese Journal of Applied Physics, 2001, 40, 5605-5609.	1.5	1
125	The fabrication and electrical properties of critical-current-modulated intrinsic Josephson junctions in Bi ₂ Sr ₂ Ca _{1-y} YCu ₂ O _x /Bi ₂ Sr ₂ CaCu ₂ O _x stacks. Superconductor Science and Technology, 2006, 19, 459-461.	3.5	1
126	Recent Progress in Downsizing FeFETs for Fe-NAND Application. Materials Research Society Symposia Proceedings, 2011, 1337, 49.	0.1	1

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127	In-Situ Growth of Bi-Sr-Ca-Cu-O Thin Films by Molecular Beam Epitaxy. , 1991, , 1085-1088.		1
128	Development of High-Endurance and Long-Retention FeFETs of Pt/CaySr1 \hat{a} \sim yBi2Ta2O9/(HfO2)x(Al2O3)1 \hat{a} \sim x/Si Gate Stacks. Topics in Applied Physics, 2020, , 23-60.	0.8	1
129	Reflection Properties of Fluxon in a Josephson Transmission Line. Japanese Journal of Applied Physics, 1987, 26, 1573.	1.5	0
130	Measurements of the high frequency loss near the plasma resonance in Josephson tunnel junctions. IEEE Transactions on Magnetics, 1987, 23, 1118-1121.	2.1	0
131	Electric-field effects in metal-insulator-superconductor diodes: possibility of singularity in capacitance-voltage relationships. Physica B: Condensed Matter, 1994, 194-196, 2399-2400.	2.7	0
132	Molecular beam epitaxial growth of BSCCO and Bi-based oxides: self-limiting growth of the Bi element. , 1998, , .		0
133	Interaction induced by nonuniform self-fields in stacks of two long Josephson junctions. IEEE Transactions on Applied Superconductivity, 1999, 9, 3953-3956.	1.7	0
134	Fabrication and electrical properties of ferroelectric-gate FETS with epitaxial gate structures. Electronics and Communications in Japan, 2004, 87, 24-33.	0.2	0
135	Composition analysis of modified layer in YBCO trilayer interface-engineered Josephson junctions. Physica C: Superconductivity and Its Applications, 2004, 412-414, 1419-1423.	1.2	0
136	Low-magnetic-field operations of intrinsic Josephson junctions with a longc-axis periodicity by artificial critical-current modulations. Superconductor Science and Technology, 2007, 20, S79-S86.	3.5	0
137	Statistical Threshold-Voltage Distribution and Elevated-Temperature Operations of Pt/SrBi$\langle inf>2$</math>Ta$\langle inf>2$</math>O$\langle inf>9$</math>/Hf-Al-O/Si MFIS FETs. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	0
138	A Ferroelectric NAND Flash Memory for Low-power and Highly Reliable Enterprise SSDs and a Ferroelectric 6T-SRAM for 0.5V Low-power CPU and SoC. Materials Research Society Symposia Proceedings, 2010, 1250, 1.	0.1	0
139	Novel Application of FeFETs to NAND Flash Memory Circuits. Topics in Applied Physics, 2016, , 271-293.	0.8	0
140	Precise understanding of ferroelectric properties in metal/ferroelectric/insulator/semiconductor FETs with (Ca,Sr)Bi$\langle inf>2$</math>Ta$\langle inf>2$</math>O$\langle inf>9$</math>. , 2017, , .		0
141	Initialize and Weak-Program Erasing Scheme for High-Performance and High-Reliability Ferroelectric NAND Flash Solid-State Drive. IEICE Transactions on Electronics, 2012, E95.C, 609-616.	0.6	0
142	Fluxon Devices. , 1984, , .		0
143	Downsizing of High-Endurance and Long-Retention Pt/CaySr1 \hat{a} \sim yBi2Ta2O9/(HfO2)x(Al2O3)1 \hat{a} \sim x/Si FeFETs. Topics in Applied Physics, 2020, , 61-77.	0.8	0
144	Novel Application of FeFETs to NAND Flash Memory Circuits. Topics in Applied Physics, 2020, , 319-341.	0.8	0